BL GALAXY ELECTRICAL

RM2Z(Z)---RM2C(Z)

PLASTIC SILICON RECTIFIER

VOLTAGE RANGE: 200 --- 1000 V
CURRENT: 1.2 A

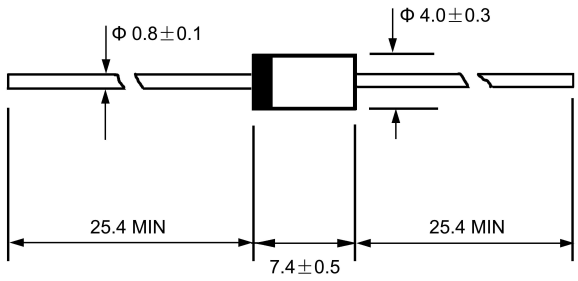
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon,Alcohol,Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO--15L,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.017 ounces,0.48 grams
- ◇ Mounting position: Any

DO - 15L



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		RM2Z	RM2	RM2A	RM2B	RM2C	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	V
Maximum average forw ard rectified current 9.5mm lead lengths, @T_A=75℃	$I_{(AV)}$	1.2					A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_j=125℃	I_{FSM}	100					A
Maximum instantaneous forw ard voltage at 1.2 A	V_F	0.91					V
Maximum reverse current @T_A=25℃	I_R	10.0					μA
at rated DC blocking voltage @T_A=100℃		50					
Typical junction capacitance (Note1)	C_J	30					pF
Typical thermal resistance (Note2)	$R_{\theta jA}$	50					℃/W
Operating junction temperature range	T_j	- 55 ---- + 150					℃
Storage temperature range	T_{STG}	- 55 ---- + 150					℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

FIG.1 -- FORWARD DERATING CURVE

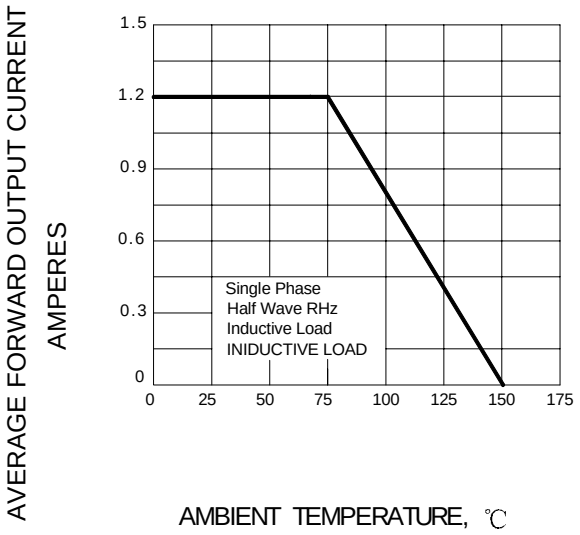


FIG.2 --PEAK FORWARD SURGE CURRENT

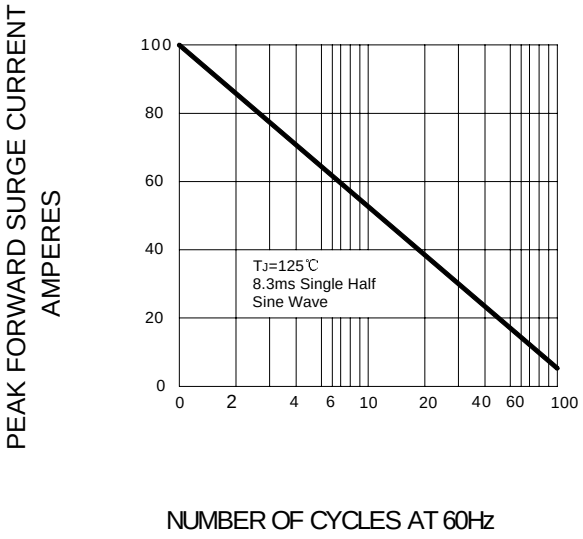


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

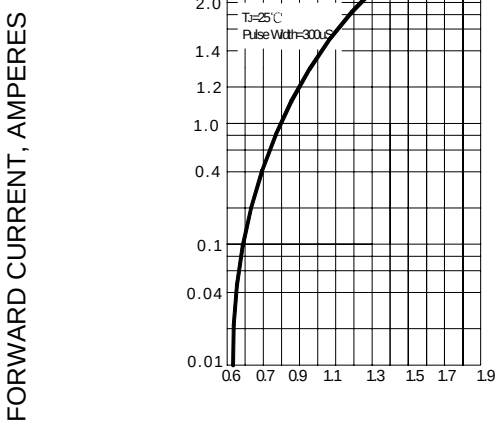


FIG.4 – TYPICAL REVERSE CHARACTERISTICS